





N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Features

- Low On-Resistance: R_{DS(ON)}
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead, Halogen and Antimony Free, RoHS Compliant "Green" Device (Notes 2, 4 and 6)
- ESD Protected Up To 2kV

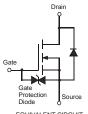
Mechanical Data

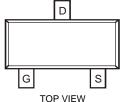
- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.008 grams (approximate)





SOT-23





EQUIVALENT CIRCUIT

Pin Out Configuration

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Units
Drain-Source Voltage		V_{DSS}	60	V
Gate-Source Voltage		V _{GSS}	±20	V
Drain Current (Note 1)	Continuous Pulsed (Note 3)		300 800	mA

Thermal Characteristics @T_A = 25°C unless otherwise specified

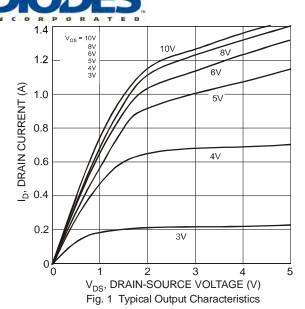
Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 1)	Pd	350	mW
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	357	°C/W
Operating and Storage Temperature Range	$T_{j,} T_{STG}$	-65 to +150	°C

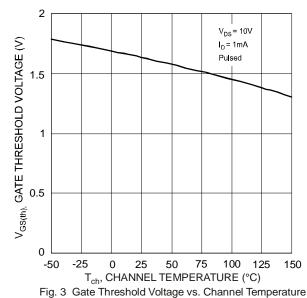
Electrical Characteristics @T_A = 25°C unless otherwise specified

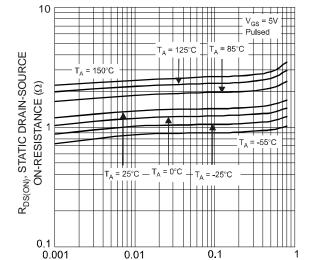
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 5)							
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$V_{GS} = 0V, I_{D} = 10\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}		_	1.0	μΑ	$V_{DS} = 60V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 5)							
Gate Threshold Voltage	$V_{GS(th)}$	1.0	1.6	2.5	V	$V_{DS} = 10V, I_{D} = 1mA$	
Static Drain-Source On-Resistance	R _{DS (ON)}	_	_	2.0		$V_{GS} = 10V, I_D = 0.5A$	
Static Dialif-Source Off-Resistance		_		3.0		$V_{GS} = 5V, I_D = 0.05A$	
Forward Transfer Admittance	Y _{fs}	80	_	_	ms	$V_{DS} = 10V, I_D = 0.2A$	
DYNAMIC CHARACTERISTICS							
Input Capacitance	C _{iss}	_	_	50	pF		
Output Capacitance	Coss	_	_	25	pF	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$	
Reverse Transfer Capacitance	C _{rss}			5.0	pF		

Notes:

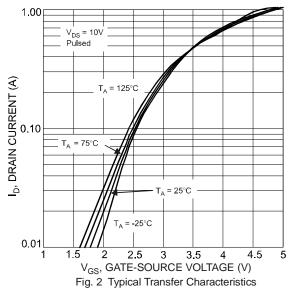
- 1. Device mounted on FR-4 PCB.
- Device mounted on FR-4 FCB.
 No purposefully added lead. Halogen and Antimony Free.
- 3. Pulse width $\leq 10 \mu S$, Duty Cycle $\leq 1\%$.
- 4. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- Short duration pulse test used to minimize self-heating effect.
- Product manufactured with Data Code V9 (week 33, 2008) and newer are built with Green Molding Compound. Product manufactured prior to Date Code V9 are built with Non-Green Molding Compound and may contain Halogens or Sb₂O₃ Fire Retardants.







I_D, DRAIN CURRENT (A)
Fig. 5 Static Drain-Source On-Resistance
vs. Drain Current



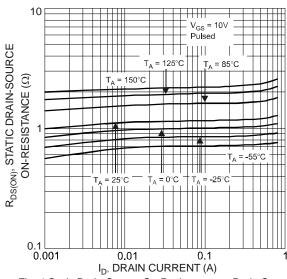


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

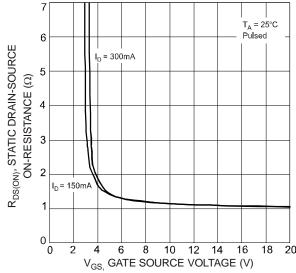
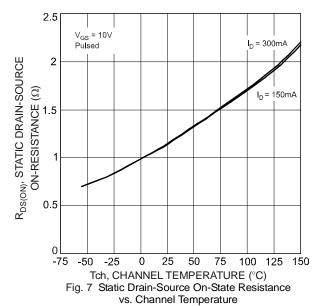
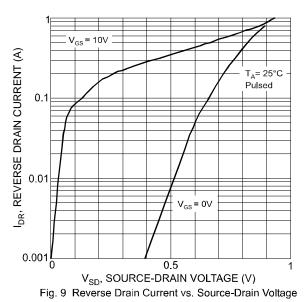
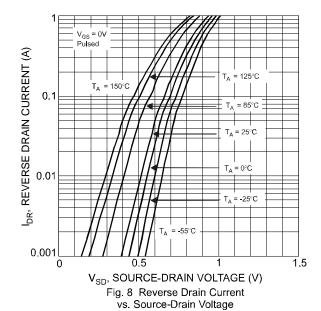


Fig. 6 Static Drain-Source On-Resistance vs. Gate-Source Voltage









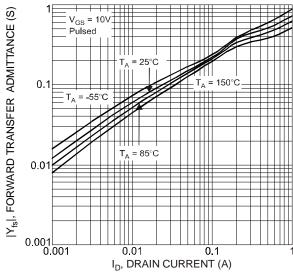


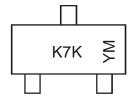
Fig.10 Forward Transfer Admittance vs. Drain Current

Ordering Information (Note 7)

Part Number	Case	Packaging
DMN601K-7	SOT-23	3000/Tape & Reel

Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



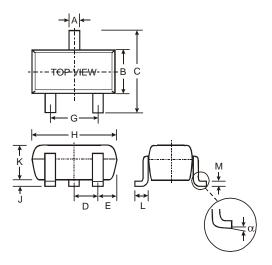
K7K = Product Type Marking Code YM = Date Code Marking Y = Year ex: S = 2005 M = Month ex: 9 = September

Date Code Key

Year	2005		2006	2007		2008	2009)	2010	2011		2012
Code	S		T	U		V	W		Χ	Υ		Z
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

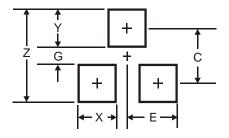


Package Outline Dimensions



	SOT-23				
Dim	Min	Max			
Α	0.37	0.51			
В	1.20	1.40			
С	2.30	2.50			
D	0.89	1.03			
E	0.45	0.60			
G	1.78	2.05			
Н	2.80	3.00			
J	0.013	0.10			
K	0.903	1.10			
L	0.45	0.61			
M	0.085	0.180			
α	0°	8°			
All Dir	All Dimensions in mm				

Suggested Pad Layout



Dimensions	Value (in mm)
Z	3.4
G	0.7
X	0.9
Υ	1.4
С	2.0
E	0.9

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